

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (currently amended): A silicon carbide epitaxial wafer which is formed on a substrate that is less than 1° off from the {0001} surface of silicon carbide having an α -type crystal structure, said silicon carbide epitaxial wafer being formed on a {0001} C face of the substrate and said substrate being a silicon carbide substrate having a flat surface and a 4H crystal structure, and further comprising a semiconductor device formed on said silicon carbide epitaxial wafer.

Claims 2-5 (canceled).

Claim 6 (previously presented): A manufacturing method of a silicon carbide epitaxial wafer, comprising the steps of:

cleansing a surface of a silicon carbide substrate with a mixed gas of hydrogen gas and propane gas at 1400°C to 1600°C to provide the substrate with a surface step of a height of 1nm or less;
epitaxially growing silicon carbide on a {0001} C face of the substrate that is less than 1° off from the {0001} surface of silicon carbide having an α -type crystal structure, the silicon carbide substrate having a 4H crystal structure; and

during said epitaxially growing step, using a source gas of silane and propane having a compositional ratio of C and Si of 1 or less and a growth pressure of 250mbar or less.

Claim 7-27 (canceled).

Claim 28 (previously presented): A silicon carbide epitaxial wafer on which a semiconductor device is formed prepared by a process comprising the steps of: cleansing a surface of a silicon carbide substrate with a mixed gas of hydrogen gas and propane gas at 1400°C to 1600°C; epitaxially growing silicon carbide on a {0001} C face of the substrate that is less than 1° off from the {0001} surface of silicon carbide having an α -type crystal structure, said silicon carbide substrate having a 4H crystal structure; and during said epitaxially growing step, using a source gas of silane and propane having a compositional ratio of C and Si of 1 or less and a growth pressure of 250mbar or less.

Claims 29-31 (canceled).

Claim 32 (previously presented): A silicon carbide epitaxial wafer according to claim 28, wherein the silicon carbide epitaxially grown on the silicon carbide substrate has the same 4H α -type crystal structure as the silicon carbide substrate.

Claim 33 (previously presented): A method according to claim 6, wherein said step of epitaxially growing silicon carbide on the silicon carbide substrate produces homoepitaxially grown silicon carbide of the same 4H α -type crystal structure as that of the silicon carbide substrate.

Claim 34 (previously presented): A silicon carbide epitaxial wafer according to claim 1, wherein said silicon carbide epitaxial wafer has the same 4H α -type crystal structure as the silicon carbide substrate.

Claim 35 (new): A silicon carbide epitaxial wafer according to claim 1, wherein said silicon carbide epitaxial wafer has a flat surface.